

NCE N-Channel Super Trench Power MOSFET



The NCEP0218K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

• V_{DS} =200V,I_D =18A

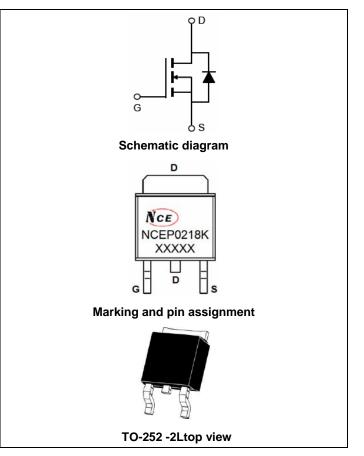
R_{DS(ON)}=145mΩ (typical) @ V_{GS}=10V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0218K	NCEP0218K	TO-252	-	-	-

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	ID	18	А
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	12.7	A
Pulsed Drain Current	I _{DM}	72	A
Maximum Power Dissipation	PD	140	W
Derating factor		0.93	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	80	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Résistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.07	°C/W]
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Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•	•		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_{D} =18A	-	145	155	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =18A	15	-	-	S
Dynamic Characteristics (Note4)			•			•
Input Capacitance	C _{lss}		-	483		PF
Output Capacitance	C _{oss}	V _{DS} =100V,V _{GS} =0V, F=1.0MHz	-	42		PF
Reverse Transfer Capacitance	C _{rss}		-	1		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	4	-	nS
Turn-on Rise Time	tr	V _{DD} =100V, R∟=8Ω	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	10	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Qg)/ _100)/1 _104	-	9.2	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =100V,I _D =18A, V _{GS} =10V	-	3.8	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	2.3	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =18A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	18	А
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =18A	-	25	-	nS
Reverse Recovery Charge	Qrr	di/dt = $100A/\mu s^{(Note3)}$	-	110	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.

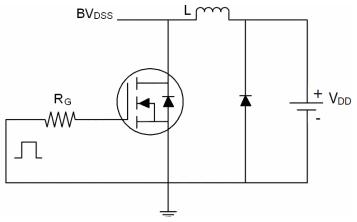
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ \!\! \mathbb{C}$,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25\Omega

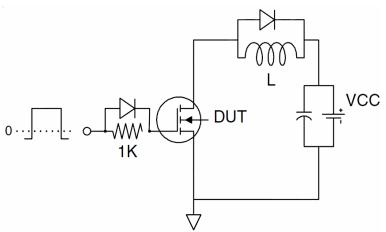


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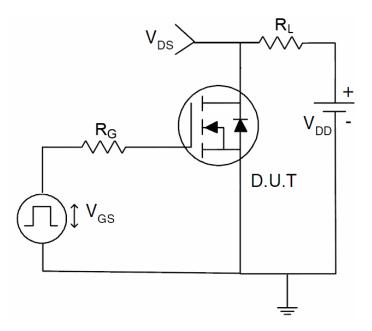
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





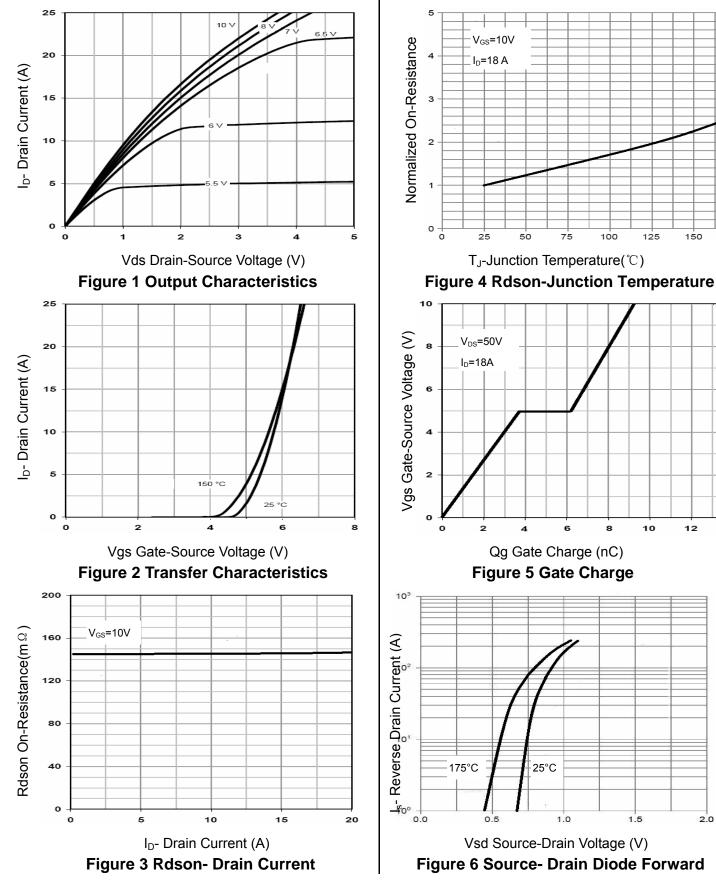
150

12

14

175

Typical Electrical and Thermal Characteristics

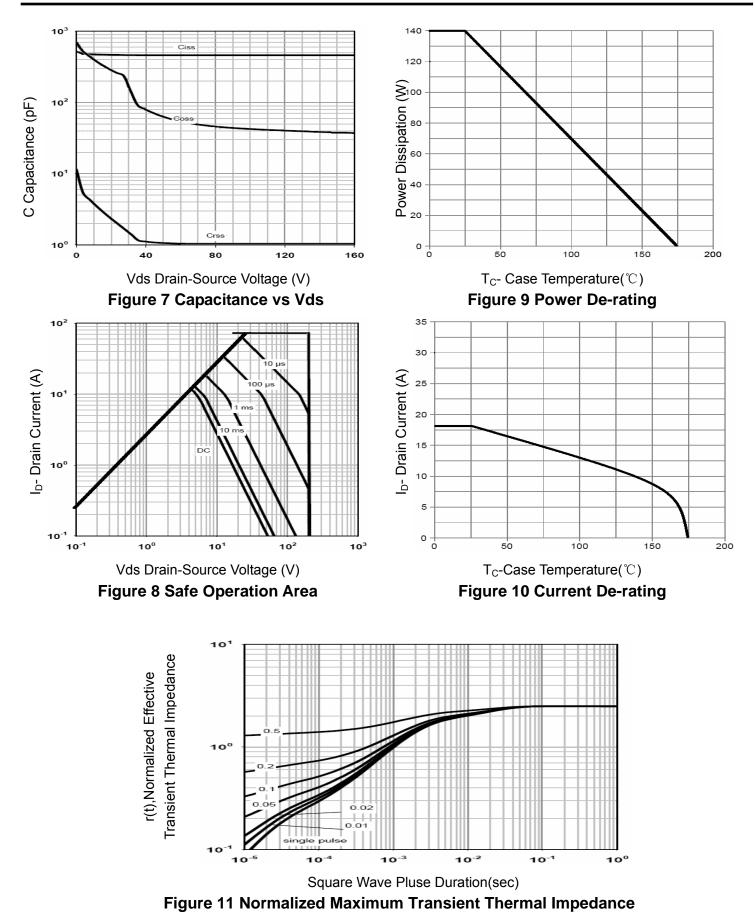


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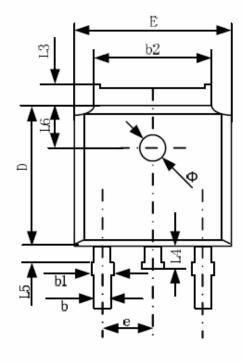
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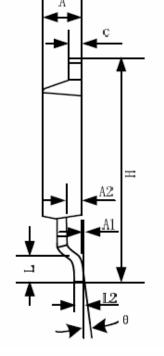
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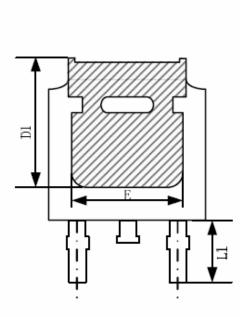




TO-252-2L Package Information







Cumhal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.20	2.38	0.087	0.094	
A1	0.00	0.10	0.000	0.004	
A2	0.90	1.10	0.035	0.043	
b	0.72	0.85	0.028	0.033	
b1	0.72	0.90	0.028	0.035	
b2	5.13	5.46	0.202	0.215	
с	0.47	0.60	0.019	0.024	
D	6.00	6.20	0.236	0.244	
D1	5.25		0.207		
E	6.50	6.70	0.256	0.264	
E1	4.70		0.185		
e	2.19	2.39	0.086	0.094	
Н	9.80	10.40	0.386	0.409	
L	1.40	1.70	0.055	0.067	
L1	2.90 REF		0.114	REF	
L2	0.508 BSC		0.020 BSC		
L3	0.90	1.25	0.035	0.049	
L4	0.60	1.00	0.024	0.039	
L5	0.15	0.75	0.006	0.030	
L6	1.80 REF		0.071 REF		
Φ	1.20	1.40	0.047	0.055	
θ	0°	8°	0°	8°	



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